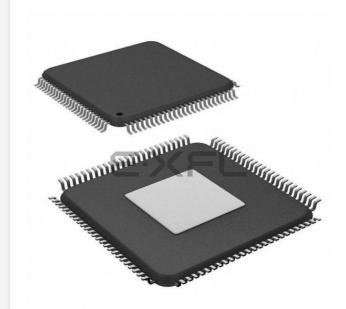
Infineon Technologies - XE164GM72F80LAAFXUMA1 Datasheet



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Applications of "<u>Embedded - Microcontrollers</u>"

Details	Obsolete
Product Status	
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
connectivity	CANbus, EBI/EMI, I ² C, LINbus, SPI, SSC, UART/USART, USI
eripherals	I ² S, POR, PWM, WDT
Number of I/O	76
Program Memory Size	576KB (576K x 8)
rogram Memory Type	FLASH
EPROM Size	-
AM Size	50K x 8
oltage - Supply (Vcc/Vdd)	3V ~ 5.5V
ata Converters	A/D 11x10b
scillator Type	Internal
perating Temperature	-40°C ~ 85°C (TA)
lounting Type	Surface Mount
ackage / Case	100-LQFP Exposed Pad
upplier Device Package	PG-LQFP-100-8
urchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe164gm72f80laafxuma1

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16-Bit

Architecture

XE164FM, XE164GM, XE164HM, XE164KM

16-Bit Single-Chip Real Time Signal Controller XE166 Family / Base Line

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Microcontrollers



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General Device Information

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
24	P5.3	I	In/A	Bit 3 of Port 5, General Purpose Input
	ADC0_CH3	I	In/A	Analog Input Channel 3 for ADC0
	T3INA	I	In/A	GPT12E Timer T3 Count/Gate Input
28	P5.4	I	In/A	Bit 4 of Port 5, General Purpose Input
	ADC0_CH4	I	In/A	Analog Input Channel 4 for ADC0
	T3EUDA	I	In/A	GPT12E Timer T3 External Up/Down Control Input
	TMS_A	I	In/A	JTAG Test Mode Selection Input
29	P5.5	I	In/A	Bit 5 of Port 5, General Purpose Input
	ADC0_CH5	I	In/A	Analog Input Channel 5 for ADC0
	CCU60_T12 HRB	I	In/A	External Run Control Input for T12 of CCU60
30	P5.8	I	In/A	Bit 8 of Port 5, General Purpose Input
	ADC0_CH8	I	In/A	Analog Input Channel 8 for ADC0
	ADC1_CH8	I	In/A	Analog Input Channel 8 for ADC1
	CCU6x_T12H RC	I	In/A	External Run Control Input for T12 of CCU60/1/2
	CCU6x_T13H RC	I	In/A	External Run Control Input for T13 of CCU60/1/2
	U2C0_DX0F	I	In/A	USIC2 Channel 0 Shift Data Input
31	P5.9	I	In/A	Bit 9 of Port 5, General Purpose Input
	ADC0_CH9	I	In/A	Analog Input Channel 9 for ADC0
	ADC1_CH9	I	In/A	Analog Input Channel 9 for ADC1
	CC2_T7IN	I	In/A	CAPCOM2 Timer T7 Count Input
32	P5.10	I	In/A	Bit 10 of Port 5, General Purpose Input
	ADC0_CH10	I	In/A	Analog Input Channel 10 for ADC0
	ADC1_CH10	I	In/A	Analog Input Channel 10 for ADC1
	BRKIN_A	I	In/A	OCDS Break Signal Input
	U2C1_DX0F	I	In/A	USIC2 Channel 1 Shift Data Input
	CCU61_T13 HRA	I	In/A	External Run Control Input for T13 of CCU61



General Device Information

 Table 5
 Pin Definitions and Functions (cont'd)

I abic	Table 3 Till Definitions and Functions (conta)									
Pin	Symbol	Ctrl.	Туре	Function						
57	P2.9	O0 / I	St/B	Bit 9 of Port 2, General Purpose Input/Output						
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output						
	TxDC1	O2	St/B	CAN Node 1 Transmit Data Output						
	CC2_CC22	O3 / I	St/B	CAPCOM2 CC22IO Capture Inp./ Compare Out.						
	A22	ОН	St/B	External Bus Interface Address Line 22						
	CLKIN1	I	St/B	Clock Signal Input 1						
	TCK_A	IH	St/B	DAPO/JTAG Clock Input If JTAG pos. A is selected during start-up, an internal pull-up device will hold this pin high when nothing is driving it. If DAP pos. 0 is selected during start-up, an internal pull-down device will hold this pin low when nothing is driving it.						
58	P0.2	O0 / I	St/B	Bit 2 of Port 0, General Purpose Input/Output						
	U1C0_SCLK OUT	O1	St/B	USIC1 Channel 0 Shift Clock Output						
	TxDC0	O2	St/B	CAN Node 0 Transmit Data Output						
	CCU61_CC6 2	О3	St/B	CCU61 Channel 2 Output						
	A2	ОН	St/B	External Bus Interface Address Line 2						
	U1C0_DX1B	I	St/B	USIC1 Channel 0 Shift Clock Input						
	CCU61_CC6 2INA	I	St/B	CCU61 Channel 2 Input						



Functional Description

8 Kbytes of on-chip Stand-By SRAM (SBRAM) provide storage for system-relevant user data that must be preserved while the major part of the device is powered down. The SBRAM is accessed via a specific interface and is powered in domain M.

1024 bytes (2 \times **512 bytes)** of the address space are reserved for the Special Function Register areas (SFR space and ESFR space). SFRs are word-wide registers which are used to control and monitor functions of the different on-chip units. Unused SFR addresses are reserved for future members of the XE166 Family. In order to ensure upward compatibility they should either not be accessed or written with zeros.

The on-chip Flash memory stores code, constant data, and control data. The on-chip Flash memory consists of 1 module of 64 Kbytes (preferably for data storage) and modules with a maximum capacity of 256 Kbytes each. Each module is organized in sectors of 4 Kbytes.

The uppermost 4-Kbyte sector of segment 0 (located in Flash module 0) is used internally to store operation control parameters and protection information.

Note: The actual size of the Flash memory depends on the chosen device type.

Each sector can be separately write protected¹⁾, erased and programmed (in blocks of 128 Bytes). The complete Flash area can be read-protected. A user-defined password sequence temporarily unlocks protected areas. The Flash modules combine 128-bit read access with protected and efficient writing algorithms for programming and erasing. Dynamic error correction provides extremely high read data security for all read access operations. Access to different Flash modules can be executed in parallel. For Flash parameters, please see Section 4.5.

Memory Content Protection

The contents of on-chip memories can be protected against soft errors (induced e.g. by radiation) by activating the parity mechanism or the Error Correction Code (ECC).

The parity mechanism can detect a single-bit error and prevent the software from using incorrect data or executing incorrect instructions.

The ECC mechanism can detect and automatically correct single-bit errors. This supports the stable operation of the system.

It is strongly recommended to activate the ECC mechanism wherever possible because this dramatically increases the robustness of an application against such soft errors.

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To save control bits, sectors are clustered for protection purposes, they remain separate for programming/erasing.



Functional Description

to a dedicated vector table location). The occurrence of a hardware trap is also indicated by a single bit in the trap flag register (TFR). Unless another higher-priority trap service is in progress, a hardware trap will interrupt any ongoing program execution. In turn, hardware trap services can normally not be interrupted by standard or PEC interrupts.

Depending on the package option up to 3 External Service Request (ESR) pins are provided. The ESR unit processes their input values and allows to implement user controlled trap functions (System Requests SR0 and SR1). In this way reset, wakeup and power control can be efficiently realized.

Software interrupts are supported by the 'TRAP' instruction in combination with an individual trap (interrupt) number. Alternatively to emulate an interrupt by software a program can trigger interrupt requests by writing the Interrupt Request (IR) bit of an interrupt control register.

3.7 On-Chip Debug Support (OCDS)

The On-Chip Debug Support system built into the XE164xM provides a broad range of debug and emulation features. User software running on the XE164xM can be debugged within the target system environment.

The OCDS is controlled by an external debugging device via the debug interface. This either consists of the 2-pin Device Access Port (DAP) or of the JTAG port conforming to IEEE-1149. The debug interface can be completed with an optional break interface.

The debugger controls the OCDS with a set of dedicated registers accessible via the debug interface (DAP or JTAG). In addition the OCDS system can be controlled by the CPU, e.g. by a monitor program. An injection interface allows the execution of OCDS-generated instructions by the CPU.

Multiple breakpoints can be triggered by on-chip hardware, by software, or by an external trigger input. Single stepping is supported, as is the injection of arbitrary instructions and read/write access to the complete internal address space. A breakpoint trigger can be answered with a CPU halt, a monitor call, a data transfer, or/and the activation of an external signal.

Tracing data can be obtained via the debug interface, or via the external bus interface for increased performance.

Tracing of program execution is supported by the XE166 Family emulation device.

The DAP interface uses two interface signals, the JTAG interface uses four interface signals, to communicate with external circuitry. The debug interface can be amended with two optional break lines.

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Functional Description

3.10 General Purpose Timer (GPT12E) Unit

The GPT12E unit is a very flexible multifunctional timer/counter structure which can be used for many different timing tasks such as event timing and counting, pulse width and duty cycle measurements, pulse generation, or pulse multiplication.

The GPT12E unit incorporates five 16-bit timers organized in two separate modules, GPT1 and GPT2. Each timer in each module may either operate independently in a number of different modes or be concatenated with another timer of the same module.

Each of the three timers T2, T3, T4 of **module GPT1** can be configured individually for one of four basic modes of operation: Timer, Gated Timer, Counter, and Incremental Interface Mode. In Timer Mode, the input clock for a timer is derived from the system clock and divided by a programmable prescaler. Counter Mode allows timer clocking in reference to external events.

Pulse width or duty cycle measurement is supported in Gated Timer Mode, where the operation of a timer is controlled by the 'gate' level on an external input pin. For these purposes each timer has one associated port pin (TxIN) which serves as a gate or clock input. The maximum resolution of the timers in module GPT1 is 4 system clock cycles.

The counting direction (up/down) for each timer can be programmed by software or altered dynamically by an external signal on a port pin (TxEUD), e.g. to facilitate position tracking.

In Incremental Interface Mode the GPT1 timers can be directly connected to the incremental position sensor signals A and B through their respective inputs TxIN and TxEUD. Direction and counting signals are internally derived from these two input signals, so that the contents of the respective timer Tx corresponds to the sensor position. The third position sensor signal TOP0 can be connected to an interrupt input.

Timer T3 has an output toggle latch (T3OTL) which changes its state on each timer overflow/underflow. The state of this latch may be output on pin T3OUT e.g. for time out monitoring of external hardware components. It may also be used internally to clock timers T2 and T4 for measuring long time periods with high resolution.

In addition to the basic operating modes, T2 and T4 may be configured as reload or capture register for timer T3. A timer used as capture or reload register is stopped. The contents of timer T3 is captured into T2 or T4 in response to a signal at the associated input pin (TxIN). Timer T3 is reloaded with the contents of T2 or T4, triggered either by an external signal or a selectable state transition of its toggle latch T3OTL. When both T2 and T4 are configured to alternately reload T3 on opposite state transitions of T3OTL with the low and high times of a PWM signal, this signal can be continuously generated without software intervention.



Functional Description

3.18 Parallel Ports

The XE164xM provides up to 76 I/O lines which are organized into 7 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in **Table 9**.

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 9 Summary of the XE164xM's Ports

Port	Width	I/O	Connected Modules
P0	8	I/O	EBC (A7A0), CCU6, USIC, CAN
P1	8	I/O	EBC (A15A8), CCU6, USIC
P2	14	I/O	EBC (READY, BHE, A23A16, AD15AD13, D15D13), CAN, CC2, GPT12E, USIC, DAP/JTAG
P4	4	I/O	EBC (CS3CS0), CC2, CAN, GPT12E, USIC
P5	11	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	3	I/O	ADC, CAN, GPT12E
P7	5	I/O	CAN, GPT12E, SCU, DAP/JTAG, CCU6, ADC, USIC
P10	16	I/O	EBC (ALE, RD, WR, AD12AD0, D12D0), CCU6, USIC, DAP/JTAG, CAN
P15	5	I	Analog Inputs, GPT12E



Electrical Parameters

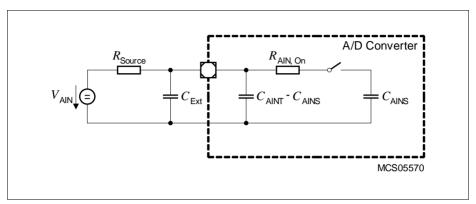


Figure 16 Equivalent Circuitry for Analog Inputs



Electrical Parameters

- 3) f_{WU} in MHz
- 4) This value includes a hysteresis of approximately 50 mV for rising voltage.
- 5) V_{LV} = selected SWD voltage level
- 6) The limit V_{LV} 0.10 V is valid for the OK1 level. The limit for the OK2 level is V_{LV} 0.15 V.

Conditions for t_{SPO} Timing Measurement

The time required for the transition from **Power-On** to **Base** mode is called t_{SPO} . It is measured under the following conditions:

Precondition: The pad supply is valid, i.e. $V_{\rm DDPB}$ is above 3.0 V and remains above 3.0 V even though the XE164xM is starting up. No debugger is attached.

Start condition: Power-on reset is removed ($\overline{PORST} = 1$).

End condition: External pin toggle caused by first user instruction executed from FLASH after startup.

Conditions for t_{SSO} Timing Measurement

The time required for the transition from **Stopover** to **Stopover Waked-Up** mode is called t_{SSO} . It is measured under the following conditions:

Precondition: The **Stopover** mode has been entered using the procedure defined in the Programmer's Guide.

Start condition: Pin toggle on ESR pin triggering the startup sequence.

End condition: External pin toggle caused by first user instruction executed from PSRAM after startup.

Coding of bit fields LEVxV in SWD and PVC Configuration Registers

Table 20 Coding of bit fields LEVxV in Register SWDCON0

Code	Default Voltage Level	Notes ¹⁾
0000 _B	2.9 V	
0001 _B	3.0 V	LEV1V: reset request
0010 _B	3.1 V	
0011 _B	3.2 V	
0100 _B	3.3 V	
0101 _B	3.4 V	
0110 _B	3.6 V	
0111 _B	4.0 V	
1000 _B	4.2 V	



Electrical Parameters

4.5 **Flash Memory Parameters**

The XE164xM is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XE164xM's Flash memory (i.e. the time after which stored

data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 22 Flash Parameters

Parameter	Symbol		Values	5	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Parallel Flash module program/erase limit	$N_{PP}SR$	_	_	41)		$N_{FL_RD} \leq 1,$ $f_{SYS} \leq 80~MHz$
depending on Flash read activity		_	_	1 ²⁾		$N_{\text{FL}_{RD}} > 1$
Flash erase endurance for security pages	N _{SEC} SR	10	-	_	cycle s	t _{RET} ≥ 20 years
Flash wait states ³⁾	N_{WSFLAS}	1	_	_		$f_{\rm SYS} \le 8 \; \rm MHz$
	_H SR	2	_	_		$f_{\rm SYS} \le$ 13 MHz
		3	_	_		$f_{\rm SYS} \leq$ 17 MHz
		4	_	_		$f_{\rm SYS}$ > 17 MHz
Erase time per sector/page	$t_{\sf ER}$ CC	_	7 ⁴⁾	8.0	ms	
Programming time per page	t _{PR} CC	_	3 ⁴⁾	3.5	ms	
Data retention time	$t_{RET}CC$	20	-	-	year s	$N_{\rm Er} \le 1~000$ cycles
Drain disturb limit	$N_{\mathrm{DD}}\mathrm{SR}$	32	-	-	cycle s	



Electrical Parameters

4.6 AC Parameters

These parameters describe the dynamic behavior of the XE164xM.

4.6.1 Testing Waveforms

These values are used for characterization and production testing (except pin XTAL1).

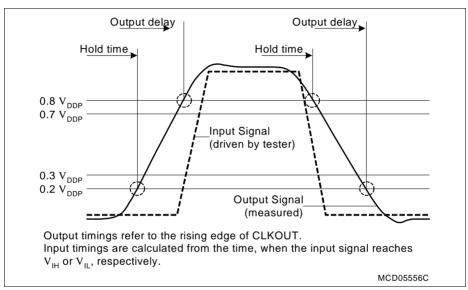


Figure 17 Input Output Waveforms

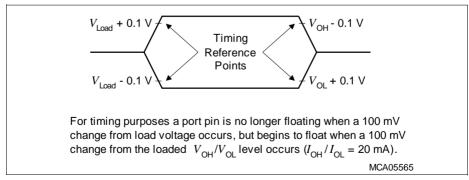


Figure 18 Floating Waveforms



Electrical Parameters

4.6.2 Definition of Internal Timing

The internal operation of the XE164xM is controlled by the internal system clock $f_{\rm SYS}$.

Because the system clock signal $f_{\rm SYS}$ can be generated from a number of internal and external sources using different mechanisms, the duration of the system clock periods (TCSs) and their variation (as well as the derived external timing) depend on the mechanism used to generate $f_{\rm SYS}$. This must be considered when calculating the timing for the XE164xM.

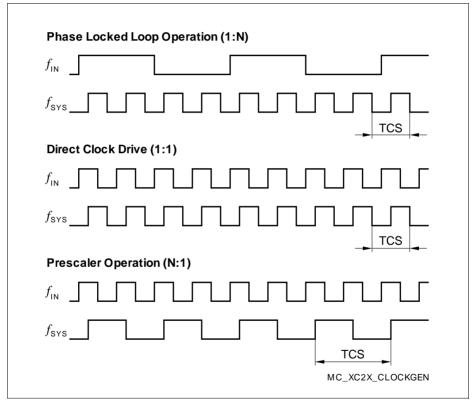


Figure 19 Generation Mechanisms for the System Clock

Note: The example of PLL operation shown in **Figure 19** uses a PLL factor of 1:4; the example of prescaler operation uses a divider factor of 2:1.

The specification of the external timing (AC Characteristics) depends on the period of the system clock (TCS).



Electrical Parameters

The timing in the AC Characteristics refers to TCSs. Timing must be calculated using the minimum TCS possible under the given circumstances.

The actual minimum value for TCS depends on the jitter of the PLL. Because the PLL is constantly adjusting its output frequency to correspond to the input frequency (from crystal or oscillator), the accumulated jitter is limited. This means that the relative deviation for periods of more than one TCS is lower than for a single TCS (see formulas and Figure 20).

This is especially important for bus cycles using waitstates and for the operation of timers, serial interfaces, etc. For all slower operations and longer periods (e.g. pulse train generation or measurement, lower baudrates, etc.) the deviation caused by the PLL jitter is negligible.

The value of the accumulated PLL jitter depends on the number of consecutive VCO output cycles within the respective timeframe. The VCO output clock is divided by the output prescaler K2 to generate the system clock signal $f_{\rm SYS}$. The number of VCO cycles is K2 × **T**, where **T** is the number of consecutive $f_{\rm SYS}$ cycles (TCS).

The maximum accumulated jitter (long-term jitter) D_{Tmax} is defined by:

$$D_{Tmax}$$
 [ns] = ±(220 / (K2 × f_{SYS}) + 4.3)

This maximum value is applicable, if either the number of clock cycles T > $(f_{SYS} / 1.2)$ or the prescaler value K2 > 17.

In all other cases for a timeframe of $T \times TCS$ the accumulated jitter D_T is determined by:

$$\mathbf{D_T}$$
 [ns] = $\mathbf{D_{Tmax}} \times$ [(1 - 0.058 × K2) × (T - 1) / (0.83 × f_{SYS} - 1) + 0.058 × K2] f_{SYS} in [MHz] in all formulas.

Example, for a period of 3 TCSs @ 33 MHz and K2 = 4:

 D_{max} = $\pm (220 \, / \, (4 \times 33)$ + 4.3) = 5.97 ns (Not applicable directly in this case!)

$$D_3 = 5.97 \times [(1 - 0.058 \times 4) \times (3 - 1) \, / \, (0.83 \times 33 - 1) + 0.058 \times 4]$$

$$= 5.97 \times [0.768 \times 2 \, / \, 26.39 \, + \, 0.232]$$

= 1.7 ns

Example, for a period of 3 TCSs @ 33 MHz and K2 = 2:

 D_{max} = $\pm (220$ / (2×33) + 4.3) = 7.63 ns (Not applicable directly in this case!)

$$D_3 = 7.63 \times [(1 - 0.058 \times 2) \times (3 - 1) \, / \, (0.83 \times 33 - 1) + 0.058 \times 2]$$

 $= 7.63 \times [0.884 \times 2 / 26.39 + 0.116]$

= 1.4 ns

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Electrical Parameters

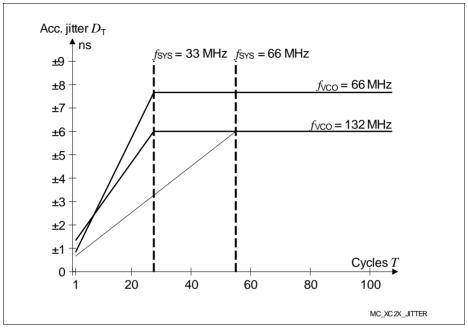


Figure 20 Approximated Accumulated PLL Jitter

Note: The specified PLL jitter values are valid if the capacitive load per pin does not exceed $C_1 = 20$ pF.

The maximum peak-to-peak noise on the pad supply voltage (measured between $V_{\rm DDPB}$ pin 100 and $V_{\rm SS}$ pin 1) is limited to a peak-to-peak voltage of $V_{\rm PP}$ = 50 mV. This can be achieved by appropriate blocking of the supply voltage as close as possible to the supply pins and using PCB supply and ground planes.



Electrical Parameters

4.6.4 Pad Properties

The output pad drivers of the XE164xM can operate in several user-selectable modes. Strong driver mode allows controlling external components requiring higher currents such as power bridges or LEDs. Reducing the driving power of an output pad reduces electromagnetic emissions (EME). In strong driver mode, selecting a slower edge reduces EME.

The dynamic behavior, i.e. the rise time and fall time, depends on the applied external capacitance that must be charged and discharged. Timing values are given for a capacitance of 20 pF, unless otherwise noted.

In general, the performance of a pad driver depends on the available supply voltage $V_{\rm DDP}$. The following table lists the pad parameters.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

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Electrical Parameters

4.6.5.1 Bus Cycle Control with the READY Input

The duration of an external bus cycle can be controlled by the external circuit using the READY input signal. The polarity of this input signal can be selected.

Synchronous READY permits the shortest possible bus cycle but requires the input signal to be synchronous to the reference signal CLKOUT.

An asynchronous READY signal puts no timing constraints on the input signal but incurs a minimum of one waitstate due to the additional synchronization stage. The minimum duration of an asynchronous READY signal for safe synchronization is one CLKOUT period plus the input setup time.

An active READY signal can be deactivated in response to the trailing (rising) edge of the corresponding command $(\overline{RD} \text{ or } \overline{WR})$.

If the next bus cycle is controlled by READY, an active READY signal must be disabled before the first valid sample point in the next bus cycle. This sample point depends on the programmed phases of the next cycle.

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Electrical Parameters

4.6.7 Debug Interface Timing

The debugger can communicate with the XE164xM either via the 2-pin DAP interface or via the standard JTAG interface.

Debug via DAP

The following parameters are applicable for communication through the DAP debug interface.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply; C_L = 20 pF.

Table 35 DAP Interface Timing for Upper Voltage Range

Parameter	Symbol Values			Unit	Note /	
		Min.	Тур.	Max.		Test Condition
DAP0 clock period	t ₁₁ SR	25 ¹⁾	_	_	ns	
DAP0 high time	t ₁₂ SR	8	_	_	ns	
DAP0 low time	t ₁₃ SR	8	_	_	ns	
DAP0 clock rise time	t ₁₄ SR	-	_	4	ns	
DAP0 clock fall time	t ₁₅ SR	-	_	4	ns	
DAP1 setup to DAP0 rising edge	t ₁₆ SR	6	_	_	ns	pad_type= stan dard
DAP1 hold after DAP0 rising edge	t ₁₇ SR	6	-	_	ns	pad_type= stan dard
DAP1 valid per DAP0 clock period ²⁾	t ₁₉ CC	17	20	_	ns	pad_type= stan dard

¹⁾ The debug interface cannot operate faster than the overall system, therefore $t_{11} \ge t_{SYS}$.

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²⁾ The Host has to find a suitable sampling point by analyzing the sync telegram response.



Electrical Parameters

Debug via JTAG

The following parameters are applicable for communication through the JTAG debug interface. The JTAG module is fully compliant with IEEE1149.1-2000.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply; C_i = 20 pF.

Table 37 JTAG Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
TCK clock period	t ₁ SR	50 ¹⁾	_	_	ns	2)
TCK high time	t ₂ SR	16	_	_	ns	
TCK low time	t_3 SR	16	_	_	ns	
TCK clock rise time	t ₄ SR	_	_	8	ns	
TCK clock fall time	t ₅ SR	_	_	8	ns	
TDI/TMS setup to TCK rising edge	t ₆ SR	6	-	-	ns	
TDI/TMS hold after TCK rising edge	t ₇ SR	6	-	-	ns	
TDO valid from TCK falling edge (propagation delay) ³⁾	t ₈ CC	_	25	29	ns	
TDO high impedance to valid output from TCK falling edge ⁴⁾³⁾	t ₉ CC	-	25	29	ns	
TDO valid output to high impedance from TCK falling edge ³⁾	t ₁₀ CC	_	25	29	ns	
TDO hold after TCK falling edge ³⁾	t ₁₈ CC	5	_	_	ns	

¹⁾ The debug interface cannot operate faster than the overall system, therefore $t_1 \ge t_{SYS}$.

²⁾ Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

³⁾ The falling edge on TCK is used to generate the TDO timing.

⁴⁾ The setup time for TDO is given implicitly by the TCK cycle time.



Electrical Parameters

Table 38 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
TCK clock period	t ₁ SR	50 ¹⁾	_	_	ns	2)
TCK high time	t ₂ SR	16	_	_	ns	
TCK low time	t ₃ SR	16	_	_	ns	
TCK clock rise time	t ₄ SR	_	_	8	ns	
TCK clock fall time	t ₅ SR	_	_	8	ns	
TDI/TMS setup to TCK rising edge	t ₆ SR	6	_	_	ns	
TDI/TMS hold after TCK rising edge	t ₇ SR	6	_	_	ns	
TDO valid from TCK falling edge (propagation delay) ³⁾	t ₈ CC	-	32	36	ns	
TDO high impedance to valid output from TCK falling edge ⁴⁾³⁾	t ₉ CC	_	32	36	ns	
TDO valid output to high impedance from TCK falling edge ³⁾	t ₁₀ CC	_	32	36	ns	
TDO hold after TCK falling edge ³⁾	t ₁₈ CC	5	_	_	ns	

¹⁾ The debug interface cannot operate faster than the overall system, therefore $t_1 \ge t_{SYS}$.

²⁾ Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

³⁾ The falling edge on TCK is used to generate the TDO timing.

⁴⁾ The setup time for TDO is given implicitly by the TCK cycle time.